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### Eğitim Bilgileri

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Yüksek Lisans, Saint-Petersburg State Technical University, Fizik, Rusya 1985 - 1987

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### Biyografi

ÖZGEÇMİŞ VE ESERLER LİSTESİ

ÖZGEÇMİŞ

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Doğum Tarihi: 08 08 1958

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Lisans	Fizik	Semerkant Devlet Üniversitesi	1980
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**Görevler:**

Görev Unvanı	Görev Yeri	Yıl
Arş.Gör.	SSCB Bilimler Akademisi, İOFFE Fizik-Teknik Elektronlu Yarıiletkenler Laboratuvarı, Rusya	Araştırma Enst. St.Petersburg, 1985-1991
Öğr.Gör.Dr.	Namangan Devlet Üniversitesi, Fizik Fakültesi,	Özbekistan 1991-1992
Yrd.Doç.Dr.	Namangan Devlet Üniversitesi, Fizik Fakültesi,	Özbekistan 1992-1994
Doç.Dr.	Namangan Devlet Üniversitesi, Fizik Fakültesi,	Özbekistan 1994-1997
Doç.Dr.	Uludağ Üniversitesi, Fen-Ed. Fak., Fizik Bölümü yabancı uyruklu öğretim üyesi)	(sözleşmeli) 1997-2004
Yrd.Doç.Dr.	Uludağ Üniversitesi, Fen-Ed. Fak., Fizik Bölümü	2004-2006
Doç.Dr.	Uludağ Üniversitesi, Fen-Ed. Fak., Fizik Bölümü	2006-2012
Prof.Dr.	Uludağ Üniversitesi, Fen-Ed. Fak., Fizik Bölümü	2012-

## Yabancı Diller

Rusça, B2 Orta Üstü

## Araştırma Alanları

Temel Bilimler

## Akademik Unvanlar / Görevler

Prof. Dr., Bursa Uludağ Üniversitesi, FEN-EDEBİYAT FAKÜLTESİ, FİZİK, 2012 - Devam Ediyor

Doç. Dr., Bursa Uludağ Üniversitesi, FEN-EDEBİYAT FAKÜLTESİ, FİZİK, 2006 - Devam Ediyor

## Yönetilen Tezler

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AHMETOĞLU M., Dar bantlı gainassb termofotovoltaik yapıların elektrik ve optik özelliklerinin incelenmesi, Doktora, B.KUCUR(Öğrenci), 2017

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## SCI, SSCI ve AHCI İndekslerine Giren Dergilerde Yayınlanan Makaleler

- I. **Simple and cost-effective wavelength measurement system using photodiode pair: Applications in fiber coupled light sources**  
AHMETOĞLU M., HACIİSMAİLOĞLU M. C., Kumbay E.  
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- II. **Narrow-band n-GaN/n-Si isotype heterojunction photodiode: A simplified approach for photodiode development**  
Olkun A., Kaplan H. K., Akay S. K., Ahmetoğlu M., Pat S., Erdogan N.  
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HACIİSMAİLOĞLU M. C., AHMETOĞLU M.  
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HACIİSMAİLOĞLU M. C., AHMETOĞLU M., ŞAFAK HACIİSMAİLOĞLU M., ALPER M., Batmaz T.  
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Kaplan H. K., Akay S. K., Ahmetoğlu M.  
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- VI. **Photodiodes for Detecting the Emission of Quantum-Sized Disc Lasers Operating in the Whispering Gallery Modes (2.2-2.3 μm)**  
Kunitsyna E., Royz M. A., Andreev I. A., Grebenshchikova E. A., Pivovarova A. A., Ahmetoglu (Afraïlov) M., Lebiadok

- Y., Mikulich R. Y., Iliinskaya N. D., Yakovlev Y. P.  
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- VIII. **Electrical and optical properties of photodiode structures formed by surface polymerization of [P (EGDMA-VPCA)-SWCNT] films on n-GaAs**  
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- IX. **N+-GaSb / no-GaInAsSb / P+-GaSb type ii heterojunction photodiodes with low radiation damage**  
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- X. **Photoelectrical properties of fabricated ZnS/Si heterojunction device using thermionic vacuum arc method**  
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- XI. **N-GaSb / no-GaInAsSb / P- GaSb Type II Heterojunction Photodiodes with Low Radiation Damage**  
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- XII. **The characteristics of ZnS/Si heterojunction diode fabricated by thermionic vacuum arc**  
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- XIII. **The electrical properties of Au/MEH-PPV:PCBM/n-type GaAs schottky barrier diode**  
Ahmetoglu (Afrailov) M., Kirsoy A., Asimov A., Kucur B.  
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- XIV. **Electrical Properties Inorganic-on-Organic Hybrid GaAs/Graphene Oxide Schottky Barrier Diode**  
Ahmetoğlu M., Kirsoy A., Okutan M., Yakuphanoglu F.  
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Ahmetoglu M., Kara A., Kucur B.  
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- XVI. **The Electrical Properties of Au/P3HT/n-Type Si Schottky Barrier Diode**  
Asimov A., Ahmetoglu M., Kirsoy A., Ozer M., Yasin M.  
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- XVII. **Electrical Characteristics and Temperature Dependence of Photovoltaic Parameters of GaInAsSb Based TPV Diode**  
Kucur B., Ahmetoglu M., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.  
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- XVIII. **The Electrical Properties of Au/P3HT/n-GaAs Schottky Barrier Diode**  
Kirsoy A., Ahmetoglu (Afrailov) M., Asimov A., Kucur B.  
ACTA PHYSICA POLONICA A, cilt.128, 2015 (SCI-Expanded)
- XIX. **Electrical and Optical Characteristics of n-GaSb/n-GaIn<sub>0.24</sub>AsSb/p-GaAl<sub>0.34</sub>AsSb Heterostructure Photodiode**  
Ahmetoglu M., Kucur B., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.  
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- XX. **Electrical Properties of GaInAsSb/GaSb/GaAlAsSb Double Heterostructure with Low Diameter**  
Kucur B., Ahmetoglu M., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.  
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- XXI. **Electrical characteristics of Al/n-type GaAs schottky barrier diodes at room temperature**

- Asimov A., Ahmetoglu M., Kucur B., Gucuyener I.  
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- XXII. **The determination of electronic parameters of Al/MDMO-PPV/P-Si/Al Schottky diode by current-voltage characteristics**  
Asimov A., Ahmetoglu (Afrailov) M.  
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- XXIII. **Gaussian Distribution of inhomogeneous barrier height in Au/n-GaP (100) Schottky barrier diodes**  
Ozer M., Guzel T., Asimov A., Ahmetoglu (Afrailov) M.  
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- XXIV. **Determination of Carrier Concentrations in P-GaSb/n-InGaAsSb Type II Misaligned Heterojunctions by the Conductivity-Magnetic Field Dependence**  
AHMETOĞLU M., Kucur B.  
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- XXV. **The determination of series resistance and interface state density distributions of Au/p-type GaAs Schottky barrier diodes**  
Asimov A., Ahmetoglu (Afrailova) M., Kucur B., Ozer M., Guzel T.  
Optoelectronics and Advanced Materials, Rapid Communications, cilt.7, ss.490-493, 2013 (SCI-Expanded)
- XXVI. **Electrical properties of GaAs-GaAlAs near infrared light emitting diodes**  
AHMETOĞLU M., Kucur B., GÜCÜYENER İ.  
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- XXVII. **Photoelectrical characteristics of GaSb/GaInAsSb/GaAlAsSb heterojunction photodiodes under illumination by photons with wavelength of 0.95-1.0  $\mu\text{m}$**   
Afrailov M.  
THIN SOLID FILMS, cilt.520, sa.15, ss.5014-5017, 2012 (SCI-Expanded)
- XXVIII. **Electrical properties of Poly(ethylene glycol dimethacrylate-n-vinyl imidazole)/Single Walled Carbon Nanotubes/n-Si Schottky diodes formed by surface polymerization of Single Walled Carbon Nanotubes**  
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- XXIX. **Electrical and optical characteristics of the InAs/InAs<sub>0.7</sub>Sb<sub>0.1</sub>P<sub>0.2</sub> single heterojunction photodiodes for the spectral range 1.6-3.5  $\mu\text{m}$**   
Ahmetoglu (Afrailov) M., Andreev I. A., Kunitsyna E. V., Moiseev K. D., Mikhailova M. P., Yakovlev Y. P.  
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- XXX. **The electrical characterization of electrodeposited Ni thin film on silicon: Schottky Barrier diodes**  
AHMETOĞLU M., Tekgul A., ALPER M., Kucur B.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.6, ss.304-306, 2012 (SCI-Expanded)
- XXXI. **Narrow gap III-V materials for infrared photodiodes and thermophotovoltaic cells**  
Kunitsyna E. V., Andreev I. A., Sherstnev V. V., L'vova T. V., Mikhailova M. P., Yakovlev Y. P., Ahmetoglu (Afrailov) M., Kaynak G., Gurler O.  
OPTICAL MATERIALS, cilt.32, sa.12, ss.1573-1577, 2010 (SCI-Expanded)
- XXXII. **Electrical and optical properties of the GaInAsSb-based heterojunctions for infrared photodiode and thermophotovoltaic cell application**  
Ahmetoglu (Afrailov) M., Kucur B., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.  
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- XXXIII. **Dark currents in GaInAsSb based heterojunction photodiodes with a low diameter area at low temperatures**  
Ahmetoglu (Afrailov) M.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.4, ss.441-444, 2010 (SCI-Expanded)

- XXXIV. **Determination of the parameters for the back-to-back switched Schottky barrier structures**  
Ahmetoglu M., Akay S. K.  
CURRENT APPLIED PHYSICS, cilt.10, sa.2, ss.652-654, 2010 (SCI-Expanded)
- XXXV. **Photoelectrical characteristics of the InAsSbP based uncooled photodiodes for the spectral range 1.6-3.5  $\mu\text{m}$**   
Afrailov M.  
INFRARED PHYSICS & TECHNOLOGY, cilt.53, sa.1, ss.29-32, 2010 (SCI-Expanded)
- XXXVI. **TO THE THEORY OF ELECTROMOTIVE FORCE GENERATED IN POTENTIAL BARRIER AT ULTRAHIGH FREQUENCY FIELD**  
Ahmetoglu (Afrailov) M., Kaynak G., Shamirzaev S., Gulyamov G., Gulyamov A., Dadamirzaev M. G., Boydeda S. R., Aprailov N.  
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- XXXVII. **Photoelectrical properties of InP-InGaAsP heterojunction avalanche photodiodes**  
Ahmetoglu M., Ozer M., Kadirov O.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.3, sa.6, ss.608-611, 2009 (SCI-Expanded)
- XXXVIII. **Current transport in GaSb /GaInAsSb/GaAlAsSb heterojunction photodiodes**  
Ahmetoglu (Afrailov) M.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.3, sa.6, ss.604-607, 2009 (SCI-Expanded)
- XXXIX. **Electron-hole interaction in spherical quantum dots of nanoheterostructures**  
Ahmetoglu (Afrailov) M., Akay S. K., Boymatov P., Inoyatov S., Ahmedov O., Rahimov N., Pulatov A.  
Optoelectronics and Advanced Materials, Rapid Communications, cilt.3, sa.3, ss.163-165, 2009 (SCI-Expanded)
- XL. **Electrical Properties of Photodiodes Based on p-GaSb/p-GaInAsSb/N-GaAlAsSb Heterojunctions**  
Ahmetoglu M., Kaynak G., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.  
TECHNICAL PHYSICS LETTERS, cilt.34, sa.11, ss.937-940, 2008 (SCI-Expanded)
- XLI. **Dark currents in GaSb/GaInAsSb heterojunction photodiodes at high temperatures**  
Ahmetoglu (Afrailov) M.  
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.10, sa.10, ss.2507-2510, 2008 (SCI-Expanded)
- XLII. **Photocurrent amplification in a isotype N+-GaSb/n(0)-GaInAsSb type II heterojunctions**  
Ahmetoglu (Afrailov) M.  
INFRARED PHYSICS & TECHNOLOGY, cilt.51, sa.6, ss.491-494, 2008 (SCI-Expanded)
- XLIII. **Temperature dependence of electrical characteristics of Cr/p-Si(100) Schottky barrier diodes**  
Erturk K., HACIİSMAİLOĞLU M. C., Bektore Y., Ahmetoglu M.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.22, sa.14, ss.2309-2319, 2008 (SCI-Expanded)
- XLIV. **Temperature dependence of electrical characteristics of Cu/n-Si Shottky barrier diodes formed by electrodeposition**  
Ahmetoglu M., Erturk K.  
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- XLV. **Electrical transport at a isotype type II heterojunctions in the system of GaSb-GaInAsSb**  
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- XLVI. **Photoelectrical characteristic of isotype N+-GaSb / no-GaInAsSb / N+- GaAlAsSb type II heterojunctions**  
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- XLVIII. **Electrical properties of n-Si/Cu Schottky diodes formed by electrodeposition**  
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- XLIX. **Avalanche photodiodes for electromagnetic calorimeters**  
Pilicer E., Kocak F., Tapan İ., Ahmetoglu (Afrailov) M.  
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DETECTORS AND ASSOCIATED EQUIPMENT, sa.1, ss.120-121, 2007 (SCI-Expanded)
- L. **Electrical properties of isotype N+-GaSb/n(0)-GaInAsSb/N+-GaAlAsSb type-II heterojunctions**  
Ahmetoglu M., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.  
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- LI. **Electrical properties of n-Si /Cu Schottky diodes formed by electrodeposition**  
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- LII. **Change in the resistance of the semiconductor in the variable deformation field**  
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- LIII. **Dark currents in the uncooled InAs / InAsSbP photodiodes for the spectral range 1.6 - 3.5 μm**  
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- LIV. **A ZnS-Si isotype heterojunction avalanche photodiode structure for scintillation light detection**  
Tapan İ., Ahmetoglu(Afrailov) M., Kocak F.  
NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION A-ACCELERATORS SPECTROMETERS  
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- LV. **Dark currents and impact ionization coefficients in the InP-InGaAsP double heterostructures**  
Ozer M., Ahmetoglu M., Aprailov N.  
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- LVI. **Electrical and photoelectrical properties of isotype N+-GaSb/n(0)-GaInAsSb type II heterojunctions**  
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INFRARED PHYSICS & TECHNOLOGY, cilt.45, sa.3, ss.169-175, 2004 (SCI-Expanded)
- LVII. **Optical Moisture Meter Based on GaInAsSb Led's and Photodiodes**  
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- LVIII. **A ZnS-Si hetero-junction photodiode for short wavelength photon detection**  
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- LIX. **Type IIGaSb based photodiodes operating in spectral range 1.5-4.8 μm at room temperature**  
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## **Akademi Dışı Deneyim**

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